

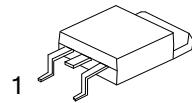
## UF5N15Z

Power MOSFET

5A, 150V N-CHANNEL  
POWER MOSFET

## ■ DESCRIPTION

The UTC **UF5N15Z** is an N-channel mode power MOSFET using UTC's advanced technology to provide customers with a minimum on-state resistance, low gate charge and superior switching performance.

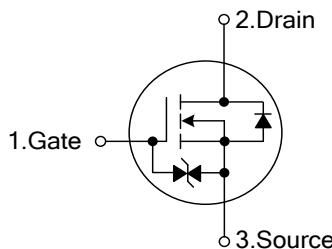


TO-252

## ■ FEATURES

- \*  $R_{DS(ON)} < 1.9\Omega$  @  $V_{GS} = 10V$ ,  $I_D = 5A$
- \* High switching speed
- \* Low gate charge

## ■ SYMBOL



## ■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UF5N15ZL-TN3-T	UF5N15ZG-TN3-T	TO-252	G	D	S	Tube
UF5N15ZL-TN3-R	UF5N15ZG-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

UF5N15ZL-TN3-R	(1)Packing Type	(1) R: Tape Reel, T: Tube
	(2)Package Type	(2) TN3: TO-252
	(3)Lead Free	(3) L: Lead Free, G: Halogen Free

■ ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS		UNIT
Drain-Source Voltage		V <sub>DSS</sub>	150		V
Gate-Source Voltage		V <sub>GSS</sub>	±20		V
Drain Current	Continuous	I <sub>D</sub>	5		A
	Pulsed	I <sub>DP</sub>	20		A
Avalanche Current		I <sub>AR</sub>	5		A
Avalanche Energy	Single Pulsed	E <sub>AS</sub>	19		mJ
Power Dissipation		P <sub>D</sub>	54		W
Junction Temperature		T <sub>J</sub>	+150		°C
Storage Temperature Range		T <sub>STG</sub>	-55~+150		°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. L=1.5mH, I<sub>AS</sub>=5A, V<sub>DD</sub>=25V, R<sub>G</sub>=25Ω, Starting T<sub>J</sub>=25°C.

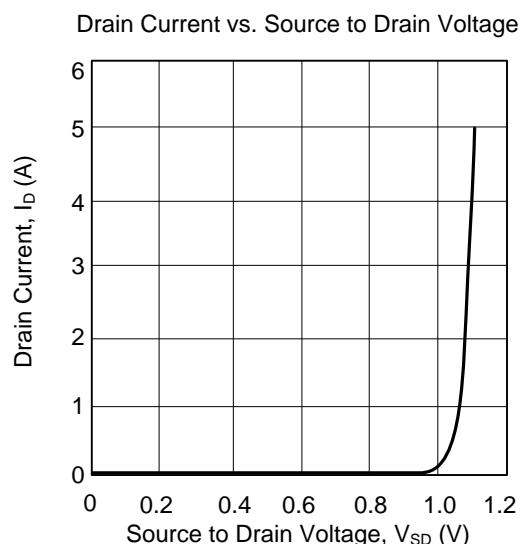
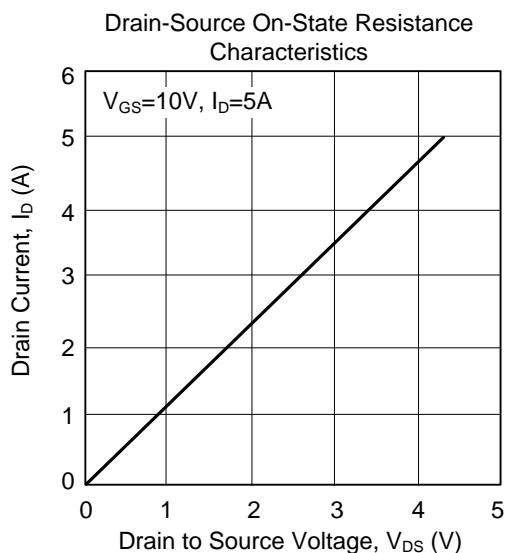
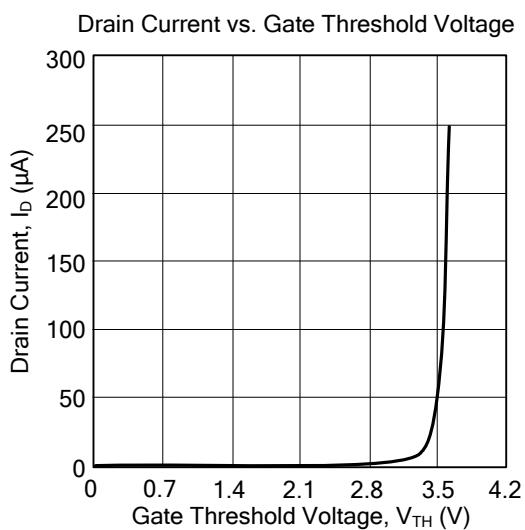
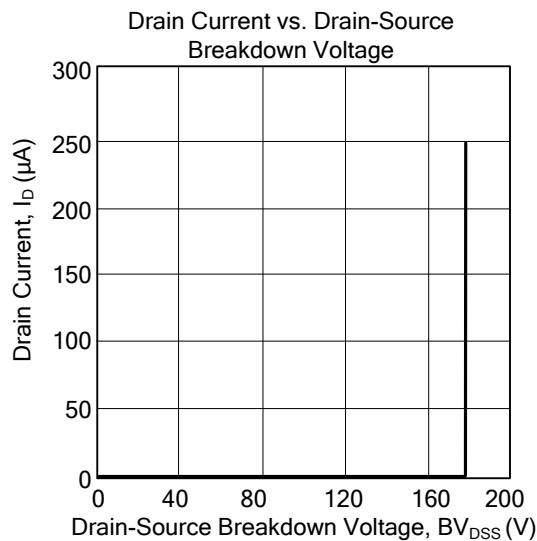
■ THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS		UNIT
Junction to Ambient	θ <sub>JA</sub>	110		°C/W
Junction to Case	θ <sub>JC</sub>	2.13		°C/W

■ ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	150			V
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =150V, V <sub>GS</sub> =0V			1	μA
Gate-Source Leakage Current	Forward	I <sub>GSS</sub>	V <sub>GS</sub> =+20V, V <sub>DS</sub> =0V		10	μA
	Reverse		V <sub>GS</sub> =-20V, V <sub>DS</sub> =0V		-10	μA
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	2		4	V
Static Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =5A	0.1		1.9	Ω
<b>DYNAMIC PARAMETERS</b>						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHz		718	955	pF
Output Capacitance	C <sub>OSS</sub>			77	105	pF
Reverse Transfer Capacitance	C <sub> RSS</sub>			3.3	5	pF
<b>SWITCHING PARAMETERS</b>						
Total Gate Charge	Q <sub>G</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =75V, I <sub>D</sub> =4.5A		10.6	15	nC
Gate to Source Charge	Q <sub>GS</sub>			3.5		nC
Gate to Drain Charge	Q <sub>GD</sub>			2.3		nC
Turn-ON Delay Time	t <sub>D(ON)</sub>	V <sub>DD</sub> =30V, I <sub>D</sub> =1A, R <sub>G</sub> =25Ω, V <sub>GS</sub> =10V		9.2	19	ns
Rise Time	t <sub>R</sub>			1.6	10	ns
Turn-OFF Delay Time	t <sub>D(OFF)</sub>			14	24	ns
Fall-Time	t <sub>F</sub>			2.9	10	ns
<b>SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS</b>						
Maximum Body-Diode Continuous Current	I <sub>S</sub>				5	A
Maximum Body-Diode Pulsed Current	I <sub>SM</sub>				20	A
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =5A, V <sub>GS</sub> =0V			1.43	V

■ TYPICAL CHARACTERISTICS



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